# Product Advisory (PA)

**Subject:** Correction to the Renesas HS0-26C31, HS0-26C32, HS0-26CLV31, HS0-26CLV32, HS0-26CT31, HS0-26CT32 Datasheets and SMDs
**Publication Date:** 10/22/2021
**Effective Date:** 10/22/2021

**Revision Description:**
Initial Release

**Description of Change:**
This notice is to inform you of Datasheet/SMD corrections as below;

1. Updates to Die Characteristics section. Die Thickness Dimension is updated on datasheet and SMD. Glassivation, M1 Thickness, M2 Thickness is only updated on datasheet, no change to SMD.

Corrections are reflected in Appendix A of the notice.

Products Impacted by the change;

| SMD # | Renesas Part# | SMD # | Renesas Part# | SMD # | Renesas Part# |
|---|---|---|---|---|---|
| 5962F9568901V9A | HS0-26C32RH-Q | 5962F9568902V9A | HS0-26CLV32RH-Q | 5962F9563201V9A | HS0-26CT31RH-Q |
| N/A | HS0-26C32RH/SAMPLE | N/A | HS0-26CLV32RH/SAMPLE | N/A | HS0-26C31RH/SAMPLE |
| 5962F9568903V9A | HS0-26C32EH-Q | 5962F9568904V9A | HS0-26CLV32EH-Q | 5962F9666301V9A | HS0-26C31RH-Q |
| 5962F9666302V9A | HS0-26CLV31RH-Q | 5962F9563101V9A | HS0-26CT32RH-Q | 5962F9666303V9A | HS0-26C31EH-Q |
| 5962F9666304V9A | HS0-26CLV31EH-Q | N/A | HS0-26CT32RH/SAMPLE | | |
| N/A | HS0-26CLV31RH/SAMPLE | 5962F9563102V9A | HS0-26CT32EH-Q | | |

**Reason for Change:**
Change corrects the datasheet and SMD to reflect the actual product characteristics. Details regarding the change are contained within Appendix A, for an updated datasheet please contact your local sales or marketing representative.

**Impact on fit, form, function, quality & reliability:**
The change will have no impact on the form, fit, function, quality, reliability and environmental compliance of the devices.

**Product Identification:**
There have been no changes to the product, this is a documentation correction only. There will be no change in the external marking of the products.

**Qualification status:** Not Applicable, correction only
**Sample availability:** 10/22/2021
**Device material declaration:** Available upon request

*Questions or requests pertaining to this change notice, including additional data or samples, must be sent to Intersil within 30 days of the publication date.*


| For additional information regarding this notice, please contact your regional change coordinator (below) | | | |
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## Appendix A:
Datasheet changes for **HS0-26C32**

### FROM:

HS-26C32RH, HS-26C32EH

**Die Characteristics**

**DIE DIMENSIONS:**
78 mils x 123 mils
(1970µm x 3120µm)

**INTERFACE MATERIALS:**

**Glassivation:**
Type: $SiO_2$
Thickness: 10kÅ ± 1kÅ

**Top Metallization:**
M1: Mo/Tiw
Thickness: 5800Å
M2: Al/Si/Cu
Thickness: 5800Å

**Worst Case Current Density:**
$<2.0 \times 10^5 A/cm^2$

**Bond Pad Size:**
110µm x 100µm

### TO:

HS-26C32RH, HS-26C32EH

**Die Characteristics**

**DIE DIMENSIONS:**
78 mils x 123 mils x 19 mils ±1 mil
(1981µm x 3124µm x 483µm ±25µm)

**INTERFACE MATERIALS:**

**Glassivation:**
Type: PSG (Phosphorus Silicon Glass)
Thickness: 8kÅ ±1kÅ

**Metallization:**
M1: Mo/TiW (Bottom)
Thickness: 5800Å ±1kÅ
M2: Al/Si/Cu (Top)
Thickness: 10kÅ ±1kÅ

**Substrate:**
AVLSI1RA

**Backside Finish:**
Silicon

**ASSEMBLY RELATED INFORMATION:**

**Substrate Potential (Powered Up):**
Internally tied to $V_{DD}$

**Worst Case Current Density:**
$< 2.0e5\ A/cm^2$

**Bond Pad Size:**
110µm x 100µm

**Transistor Count:**
315

## Datasheet changes for **HS0-26C31**

### FROM:

HS-26C31RH, HS-26C31EH

**Die Characteristics**

**DIE DIMENSIONS:**
96.5 mils x 195 mils x 21 mils
(2450 x 4950)

**INTERFACE MATERIALS:**

**Glassivation:**
Type: PSG (Phosphorus Silicon Glass)
Thickness: 10kÅ ±1kÅ

**Metallization:**
M1: Mo/TiW
Thickness: 5800Å
M2: Al/Si/Cu (Top)
Thickness: 10kÅ ±1kÅ

**Substrate:**
AVLSI1RA

**Backside Finish:**
Silicon

**ASSEMBLY RELATED INFORMATION:**

**Substrate Potential (Powered Up):**
$V_{DD}$

**ADDITIONAL INFORMATION:**

**Worst Case Current Density:**
$<2.0x10^5 A/cm^2$

**Bond Pad Size:**
110µmx100µm

### TO:

HS-26C31RH, HS-26C31EH

**Die Characteristics**

**DIE DIMENSIONS:**
96.5 mils x 195 mils x 19 mils ±1mil
(2451µm x 4953µm x 483µm ±25µm)

**INTERFACE MATERIALS:**

**Glassivation:**
Type: PSG (Phosphorus Silicon Glass)
Thickness: 8kÅ ±1kÅ

**Metallization:**
M1: Mo/TiW (Bottom)
Thickness: 5800Å ±1kÅ
M2: Al/Si/Cu (Top)
Thickness: 10kÅ ±1kÅ

**Substrate:**
AVLSI1RA

**Backside Finish:**
Silicon

**ASSEMBLY RELATED INFORMATION:**

**Substrate Potential (Powered Up):**
Internally tied to $V_{DD}$

**ADDITIONAL INFORMATION:**

**Worst Case Current Density:**
$<2.0x10^5 A/cm^2$

**Bond Pad Size:**
110µmx100µm

## Datasheet changes for HS0-26CLV31

### FROM:

HS-26CLV31RH, HS-26CLV31EH

**Die Characteristics**

**DIE DIMENSIONS:**
96.5 mils x 195 mils x 21 mils
(2450 x 4950)

**INTERFACE MATERIALS:**

**Glassivation:**
Type: PSG (Phosphorus Silicon Glass)
Thickness: 8kÅ ±1kÅ

**Metallization:**
Bottom: Mo/TiW
Thickness: 5800Å ±1kÅ
Top: AlSiCu (Top)
Thickness: 10kÅ ±1kÅ

**Substrate:**
AVLSI1RA

**Backside Finish:**
Silicon

**ASSEMBLY RELATED INFORMATION:**

**Substrate Potential (Powered Up):**
$V_{DD}$

**ADDITIONAL INFORMATION:**

**Worst Case Current Density:**
$<2.0x10^5 A/cm^2$

**Bond Pad Size:**
110µmx100µm

### TO:

HS-26CLV31RH, HS-26CLV31EH

**Die Characteristics**

**DIE DIMENSIONS:**
96.5 mils x 195 mils x 19 mils ±1mil
2451µm x 4953µm x 483µm ±25µm

**INTERFACE MATERIALS:**

**Glassivation:**
Type: PSG (Phosphorus Silicon Glass)
Thickness: 8kÅ ±1kÅ

**Metallization:**
M1: Mo/TiW (Bottom)
Thickness: 5800Å ±1kÅ
M2: AlSiCu (Top)
Thickness: 10kÅ ±1kÅ

**Substrate:**
AVLSI1RA

**Backside Finish:**
Silicon

**ASSEMBLY RELATED INFORMATION:**

**Substrate Potential (Powered Up):**
Internally tied to $V_{DD}$

**ADDITIONAL INFORMATION:**

**Worst Case Current Density:**
$<2.0x10^5 A/cm^2$

**Bond Pad Size:**
110µmx100µm

## Datasheet changes for HS0-26CLV32

### FROM:

HS-26CLV32RH, HS-26CLV32EH

**Die Characteristics**

**DIE DIMENSIONS:**
78 mils x 123 mils x 21 mils
(1970µm x 3120µm)

**INTERFACE MATERIALS:**

**Glassivation:**
Type: PSG (Phosphorus Silicon Glass)
Thickness: 8kÅ ±1kÅ

**Substrate:**
AVLSI1RA, Silicon backside, $V_{DD}$ backside potential

**Metallization:**
Bottom: Mo/TiW
Thickness: 5800Å ±1kÅ
Top: Al/Si/Cu
Thickness: 10kÅ ±1kÅ

**Worst Case Current Density:**
$<2.0 \times 10^5 A/cm^2$

**Bond Pad Size:**
110µmx100µm

### TO:

HS-26CLV32RH, HS-26CLV32EH

**Die Characteristics**

**DIE DIMENSIONS:**
78 mils x 123 mils x 19mils ±1mil
(1981µm x 3124µm x 483µm ±25µm)

**INTERFACE MATERIALS:**

**Glassivation:**
Type: PSG (Phosphorus Silicon Glass)
Thickness: 8kÅ ±1kÅ

**Metallization:**
M1: Mo/TiW (Bottom)
Thickness: 5800Å ±1kÅ
M2: Al/Si/Cu (Top)
Thickness: 10kÅ ±1kÅ

**Substrate:**
AVLSI1RA

**Backside Finish:**
Silicon

**ASSEMBLY RELATED INFORMATION:**

**Substrate Potential (Powered Up):**
Internally tied to $V_{DD}$

**Worst Case Current Density:**
$< 2.0e5 A/cm^2$

**Bond Pad Size:**
110µm x 100µm

**Transistor Count:**
315

Datasheet changes for **HS0-26CT32**

## FROM:

HS-26CT32RH, HS-26CT32EH

### Die Characteristics

**DIE DIMENSIONS:**
78 mils x 123 mils
(1970µm x 3120µm)

**INTERFACE MATERIALS:**

**Glassivation:**
Type: PSG (Phosphorus Silicon Glass)
Thickness: 10kÅ ±1kÅ

**Top Metallization:**
M1: Mo/Tiw
Thickness: 5800Å
M2: Al/Si/Cu
Thickness: 10kÅ ±1kÅ

**Substrate:**
AVLSI1RA

**Backside Finish:**
Silicon

**ASSEMBLY RELATED INFORMATION:**

**Substrate Potential:**
$V_{DD}$ (When Powered Up)

**ADDITIONAL INFORMATION:**

**Worst Case Current Density:**
$<2.0 \times 10^5 A/cm^2$

**Transistor Count:**
240

**Bond Pad Size:**
110µm x 100µm

## TO:

HS-26CT32RH, HS-26CT32EH

### Die Characteristics

**DIE DIMENSIONS:**
78 mils x 123 mils x 19mils ±1mil
(1981µm x 3124µm x 483µm ±25µm)

**INTERFACE MATERIALS:**

**Glassivation:**
Type: PSG (Phosphorus Silicon Glass)
Thickness: 8kÅ ±1kÅ

**Metallization:**
M1: Mo/TiW (Bottom)
Thickness: 5800Å ±1kÅ
M2: Al/Si/Cu (Top)
Thickness: 10kÅ ±1kÅ

**Substrate:**
AVLSI1RA

**Backside Finish:**
Silicon

**ASSEMBLY RELATED INFORMATION:**

**Substrate Potential (Powered Up):**
Internally tied to $V_{DD}$

**Worst Case Current Density:**
$< 2.0e5\ A/cm^2$

**Bond Pad Size:**
110µm x 100µm

**Transistor Count:**
315

Datasheet changes for **HS0-26CT31**

## FROM:

HS-26CT31RH, HS-26CT31EH

### Die Characteristics

**DIE DIMENSIONS:**
96.5 milx195 milsx21 mils
(2450x4950)

**INTERFACE MATERIALS:**

**Glassivation:**
Type: PSG (Phosphorus Silicon Glass)
Thickness: 10kÅ ± 1kÅ

**Metallization:**
M1: Mo/TiW
Thickness: 5800Å
M2: Al/Si/Cu (Top)
Thickness: 10kÅ ±1kÅ

**Substrate:**
AVLSI1RA

**Backside Finish:**
Silicon

**ASSEMBLY RELATED INFORMATION:**

**Substrate Potential (Powered Up):**
$V_{DD}$

**ADDITIONAL INFORMATION:**

**Worst Case Current Density:**
$<2.0x10^5 A/cm^2$

**Bond Pad Size:**
110µmx100µm

## TO:

HS-26CT31RH, HS-26CT31EH

### Die Characteristics

**DIE DIMENSIONS:**
96.5 mils x 195 mils x 19 mils ±1mil
2451µm x 4953µm x 483µm ±25µm

**INTERFACE MATERIALS:**

**Glassivation:**
Type: PSG (Phosphorus Silicon Glass)
Thickness: 8kÅ ±1kÅ

**Metallization:**
M1: Mo/TiW (Bottom)
Thickness: 5800Å ±1kÅ
M2: Al/Si/Cu (Top)
Thickness: 10kÅ ±1kÅ

**Substrate:**
AVLSI1RA

**Backside Finish:**
Silicon

**ASSEMBLY RELATED INFORMATION:**

**Substrate Potential (Powered Up):**
Internally tied to $V_{DD}$

**ADDITIONAL INFORMATION:**

**Worst Case Current Density:**
$<2.0x10^5 A/cm^2$

**Bond Pad Size:**
110µmx100µm

## Summary

| SMD # | Renesas Part# | Die Dimension | | Glassivation type/thickness | | M1 Thickness | | M2 Thickness | |
|---|---|---|---|---|---|---|---|---|---|
| | | OLD | NEW | OLD | NEW | OLD | NEW | OLD | NEW |
| 5962F9568901V9A | HS0-26C32RH-Q | Datasheet=78 x 123 x 21 mils SMD=78 x 123 x 21 mils | 78 x 123 x 19mils +/-1mil | SiO2 10kA +/-1kA | PSG 8kA +/-1kA | 5800A | 5800A +/-1kA | 5800A | 10kA +/-1kA |
| N/A | HS0-26C32RH/SAMPLE | | | | | | | | |
| 5962F9568903V9A | HS0-26C32EH-Q | | | | | | | | |
| 5962F9666302V9A | HS0-26CLV31RH-Q | Datasheet=96.5 x 195 x 21 mils SMD=96.5 x 195 x 21 mils | 96.5 x 195 x 19 mils +/-1mil | No Change | No Change | No Change | No Change | No Change | No Change |
| 5962F9666304V9A | HS0-26CLV31EH-Q | | | | | | | | |
| N/A | HS0-26CLV31RH/SAMPLE | | | | | | | | |
| 5962F9568902V9A | HS0-26CLV32RH-Q | Datasheet=78 x 123 x 21 mils SMD=78 x 123 x 21 mils | 78 x 123 x 19 mils +/-1mil | No Change | No Change | No Change | No Change | No Change | No Change |
| N/A | HS0-26CLV32RH/SAMPLE | | | | | | | | |
| 5962F9568904V9A | HS0-26CLV32EH-Q | | | | | | | | |
| 5962F9563101V9A | HS0-26CT32RH-Q | Datasheet=78 x 123 x 21 mils SMD=78 x 123 x 21 mils | 78 x 123 x 19mils +/-1mil | PSG 10kA +/-1kA | PSG 8kA +/-1kA | 5800A | 5800A +/-1kA | No Change | No Change |
| N/A | HS0-26CT32RH/SAMPLE | | | | | | | | |
| 5962F9563102V9A | HS0-26CT32EH-Q | | | | | | | | |
| 5962F9563201V9A | HS0-26CT31RH-Q | Datasheet=96.5 x 195 x 21 mils | 96.5 x 195 x 19 mils +/-1mil | PSG 10kA +/-1kA | PSG 8kA +/-1kA | 5800A | 5800A +/-1kA | No Change | No Change |
| N/A | HS0-26C31RH/SAMPLE | Datasheet=96.5 x 195 x 21 mils SMD=96.5 x 195 x 21 mils | 96.5 x 195 x 19 mils +/-1mil | PSG 10kA +/-1kA | PSG 8kA +/-1kA | 5800A | 5800A +/-1kA | No Change | No Change |
| 5962F9666301V9A | HS0-26C31RH-Q | | | | | | | | |
| 5962F9666303V9A | HS0-26C31EH-Q | | | | | | | | |